TY Semicondutor®

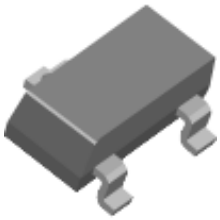
Product specification

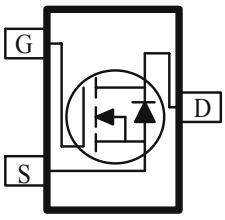
AM2310N

These miniature surface mount MOSFETs utilize High Cell Density process. Low $r_{DS(on)}$ assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are lower voltage application, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low $r_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Fast Switch
- Low Gate Charge
- Miniature SOT-23 Surface Mount Package Saves Board Space

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.065 @ V_{GS} = 4.5V	2.2
	0.082 @ V_{GS} = 2.5V	2.0





ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±8	
Continuous Drain Current[a]	T_A=25°C	I_D	2.2	A
	T_A=70°C		1.7	
Pulsed Drain Current[b]		I_{DM}	10	
Continuous Source Current (Diode Conduction)[a]		I_S	0.45	A
Power Dissipation[a]	T_A=25°C	P_D	0.5	W
	T_A=70°C		0.42	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient[a]	t <= 5 sec	R_{THJA}	250	°C/W
	Steady-State		285	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Conditions**	**Limits**			**Unit**
			Min	**Typ**	**Max**	
Switch Off Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 uA	30			
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24 V, V_{GS} = 0 V			1	µA
		V_{DS} = 24 V, V_{GS} = 0 V, T_J = 55°C			10	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8 V			±100	nA
Switch On Characteristics						
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 uA	0.43	0.7	1.0	V
On-State Drain Current[A]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 4.5 V	10			A
Drain-Source On-Resistance[A]	$r_{DS(on)}$	V_{GS} = 4.5 V, I_D = 2.2 A		54	65	mΩ
		V_{GS} = 4.5 V, I_D = 2.2 A TJ = 55°C		80	99	
		V_{GS} = 2.5 V, I_D = 2.0 A		70	82	
Forward Tranconductance[A]	g_{fs}	V_{DS} = 5 V, I_D = 2.2 A		13		S
Diode Forward Voltage	V_{SD}	I_S = 0.45 A, V_{GS} = 0 V		0.65	1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 2.2 A		7.0	9.0	nC
Gate-Source Charge	Q_{gs}			1.1		
Gate-Drain Charge	Q_{gd}			1.9		
Switching						
Turn-On Delay Time	$t_{d(on)}$	V_{DS} = 10 V, I_D = 1 A, R_G = 6 Ω, V_{GEN} = 4.5 V		4	11	ns
Rise Time	t_r			11	19	
Turn-Off Delay Time	$t_{d(off)}$			18	30	
Fall-Time	t_f			5	10	

Notes

a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.